



# STD85N3LH5 STP85N3LH5, STU85N3LH5

N-channel 30 V, 0.0042  $\Omega$  , 80 A, DPAK, TO-220, IPAK  
STripFET™ V Power MOSFET

## Features

Type	V <sub>DSS</sub>	R <sub>DS(on)</sub> max.	I <sub>D</sub>
STD85N3LH5	30 V	< 0.005 $\Omega$	80 A
STP85N3LH5			
STU85N3LH5			

- R<sub>DS(on)</sub> \* Q<sub>g</sub> industry benchmark
- Extremely low on-resistance R<sub>DS(on)</sub>
- High avalanche ruggedness
- Low gate drive power losses

## Application

Switching applications

## Description

This product utilizes the 5<sup>th</sup> generation of design rules of ST's proprietary STripFET™ technology. The lowest available R<sub>DS(on)</sub> \* Q<sub>g</sub>, in the standard packages, makes this device suitable for the most demanding DC-DC converter applications, where high power density is to be achieved.

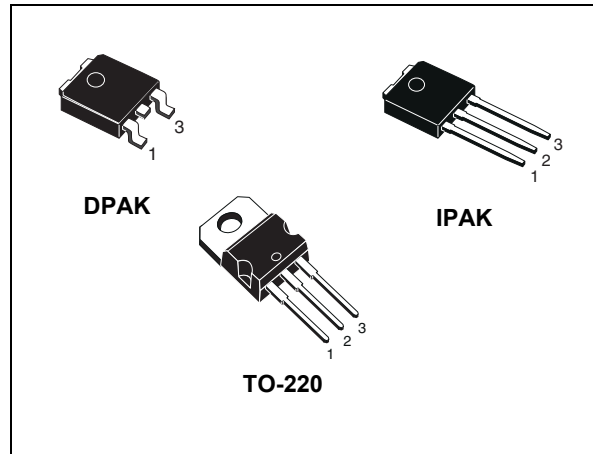


Figure 1. Internal schematic diagram

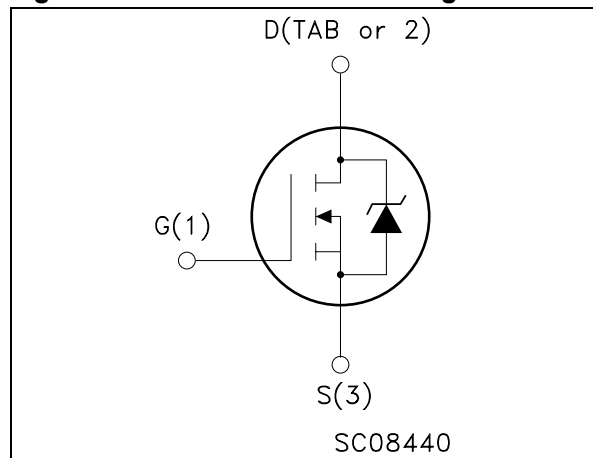


Table 1. Device summary

Order codes	Marking	Package	Packaging
STD85N3LH5	85N3LH5	DPAK	Tape and reel
STP85N3LH5		TO-220	Tube
STU85N3LH5		IPAK	

# Contents

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage ( $V_{GS} = 0$ )	30	V
$V_{DS}$	Drain-source voltage ( $V_{GS} = 0$ ) @ $T_{JMAX}$	35	V
$V_{GS}$	Gate-source voltage	$\pm 22$	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	80	A
$I_D$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	55	A
$I_{DM}^{(2)}$	Drain current (pulsed)	320	A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	70	W
	Derating factor	0.47	W/ $^\circ\text{C}$
$E_{AS}^{(3)}$	Single pulse avalanche energy	165	mJ
$T_{stg}$	Storage temperature	-55 to 175	$^\circ\text{C}$
$T_j$	Max. operating junction temperature	175	$^\circ\text{C}$

1. Limited by wire bonding
2. Pulse width limited by safe operating area
3. Starting  $T_j = 25\text{ }^\circ\text{C}$ ,  $I_D = 40\text{ A}$ ,  $V_{DD} = 25\text{ V}$

**Table 3. Thermal resistance**

Symbol	Parameter	Value			Unit
		TO-220	DPAK	IPAK	
$R_{thj-case}$	Thermal resistance junction-case max	2.14			$^\circ\text{C/W}$
$R_{thj-amb}$	Thermal resistance junction-amb max	62.5		100	$^\circ\text{C/W}$
$R_{thj-pcb}$	Thermal resistance junction-pcb max		100		$^\circ\text{C/W}$
$T_l$	Maximum lead temperature for soldering purpose	275			$^\circ\text{C}$

## 2 Electrical characteristics

( $T_{CASE} = 25\text{ °C}$  unless otherwise specified)

**Table 4. Static**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown Voltage	$I_D = 250\ \mu\text{A}$ , $V_{GS} = 0$	30			V
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = 30\text{ V}$ $V_{DS} = 30\text{ V}$ , $T_c = 125\text{ °C}$			1 10	$\mu\text{A}$ $\mu\text{A}$
$I_{GSS}$	Gate body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 22\text{ V}$			$\pm 100$	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 250\ \mu\text{A}$	1	1.8	2.5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}$ , $I_D = 40\text{ A}$ SMD version		0.042	0.005	$\Omega$
		$V_{GS} = 10\text{ V}$ , $I_D = 40\text{ A}$		0.0046	0.0054	$\Omega$
		$V_{GS} = 5\text{ V}$ , $I_D = 40\text{ A}$ SMD version		0.0052	0.0065	$\Omega$
		$V_{GS} = 5\text{ V}$ , $I_D = 40\text{ A}$		0.0058	0.0071	$\Omega$

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 25\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0$		1850		pF
$C_{oss}$	Output capacitance			380		pF
$C_{rss}$	Reverse transfer capacitance			58		pF
$Q_g$	Total gate charge	$V_{DD} = 15\text{ V}$ , $I_D = 80\text{ A}$		14		nC
$Q_{gs}$	Gate-source charge	$V_{GS} = 5\text{ V}$		6.8		nC
$Q_{gd}$	Gate-drain charge	<a href="#">Figure 16</a>		4.7		nC
$Q_{gs1}$	Pre $V_{th}$ gate-to-source charge	$V_{DD} = 15\text{ V}$ , $I_D = 80\text{ A}$		2.3		nC
$Q_{gs2}$	Post $V_{th}$ gate-to-source charge	$V_{GS} = 5\text{ V}$ <a href="#">Figure 16</a>		4.5		nC
$R_G$	Gate input resistance	$f = 1\text{ MHz}$ gate bias Bias = 0 test signal level = 20 mV open drain		1.2		$\Omega$

**Table 6. Switching on/off (inductive load)**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 15\text{ V}$ , $I_D = 40\text{ A}$ , $R_G = 4.7\ \Omega$ , $V_{GS} = 5\text{ V}$ <i>Figure 15</i>		6		ns
$t_r$	Rise time			14		ns
$t_{d(off)}$	Turn-off delay time	<i>Figure 15</i>		23.6		ns
$t_f$	Fall time			10.8		ns

**Table 7. Source drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current				80	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				320	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 40\text{ A}$ , $V_{GS} = 0$			1.1	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 80\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD} = 20\text{ V}$ <i>Figure 17</i>		31.8		ns
$Q_{rr}$	Reverse recovery charge			26.1		nC
$I_{RRM}$	Reverse recovery current			1.6		A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

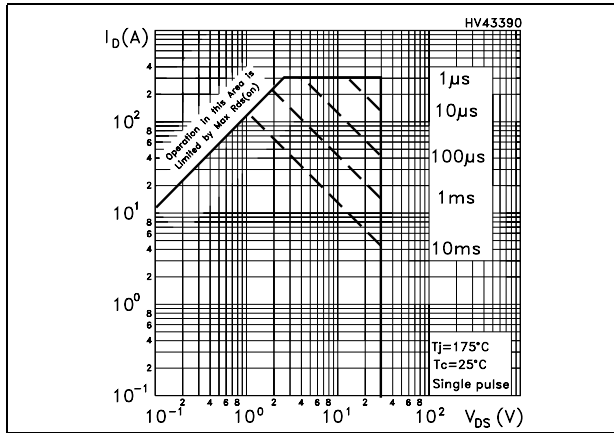


Figure 3. Thermal impedance

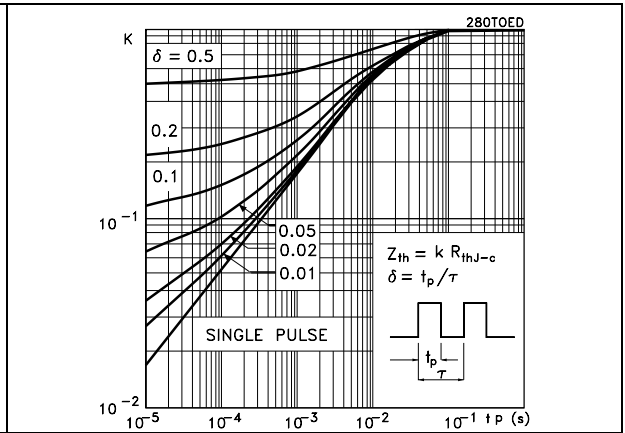


Figure 4. Output characteristics

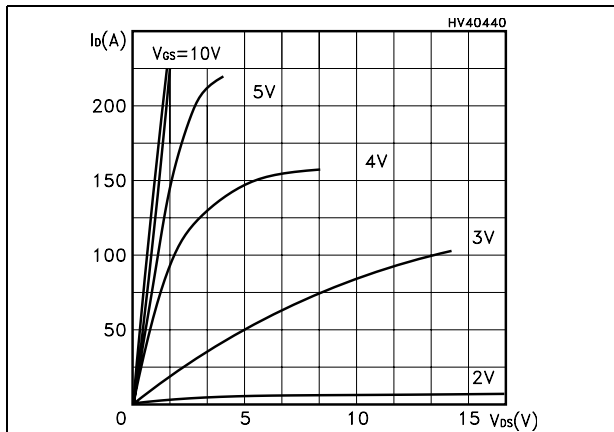


Figure 5. Transfer characteristics

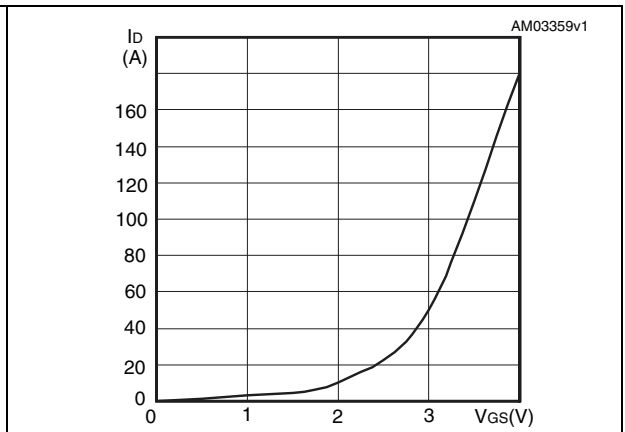


Figure 6. Normalized  $B_{V_{DSS}}$  vs temperature

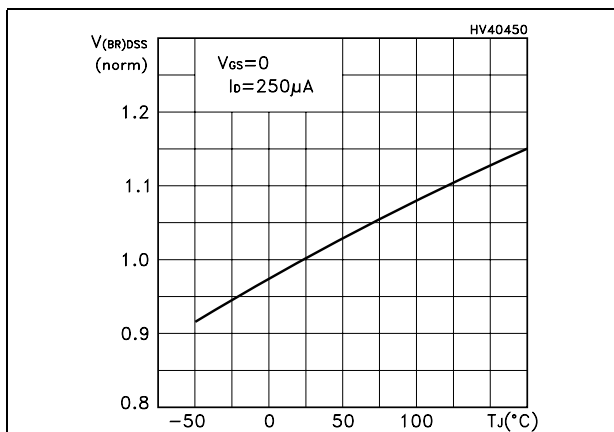


Figure 7. Static drain-source on resistance

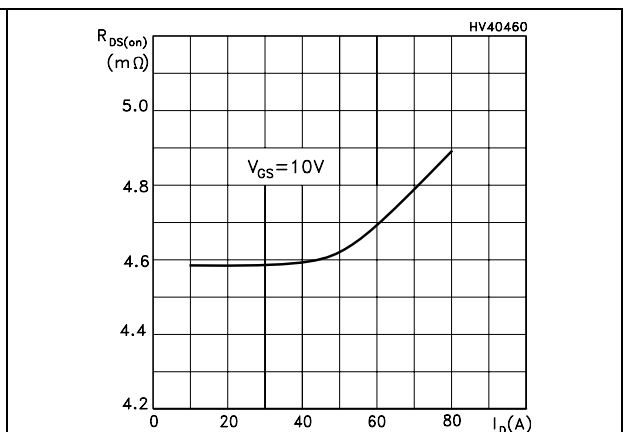


Figure 8. Gate charge vs gate-source voltage Figure 9. Capacitance variations

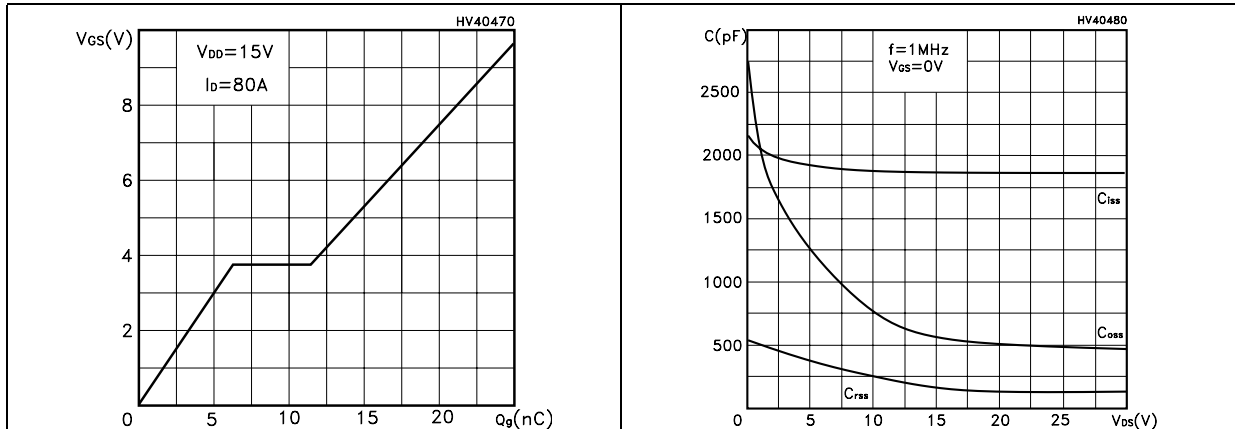


Figure 10. Normalized gate threshold voltage vs temperature Figure 11. Normalized on resistance vs temperature

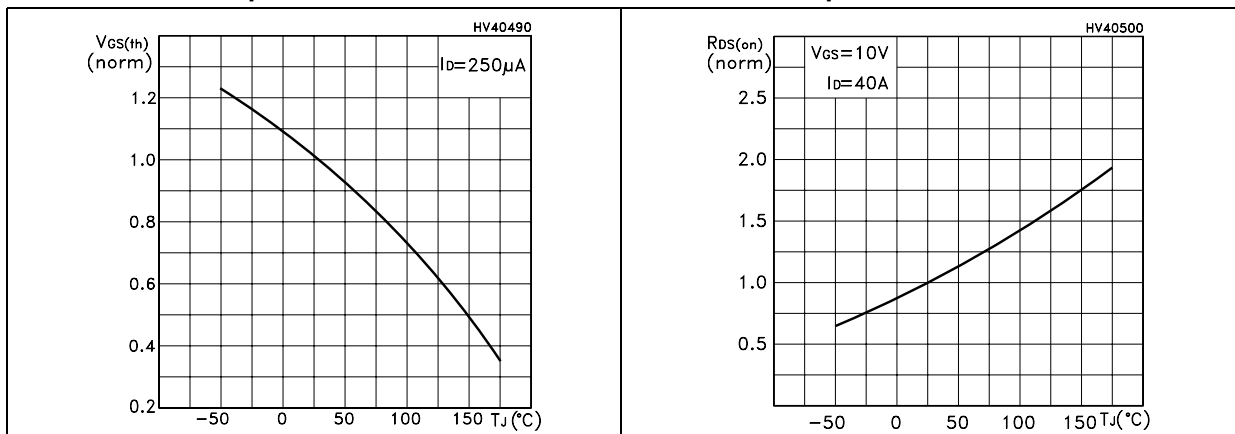
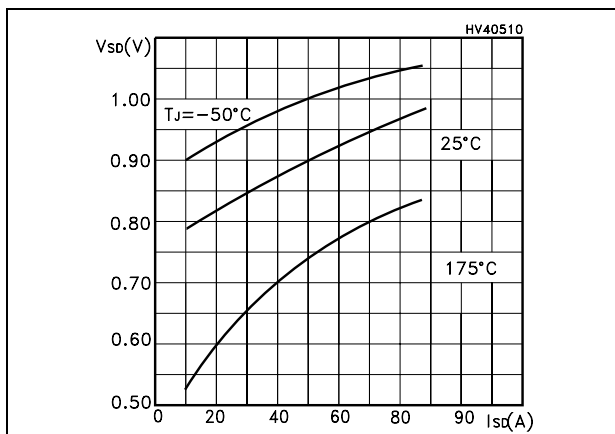
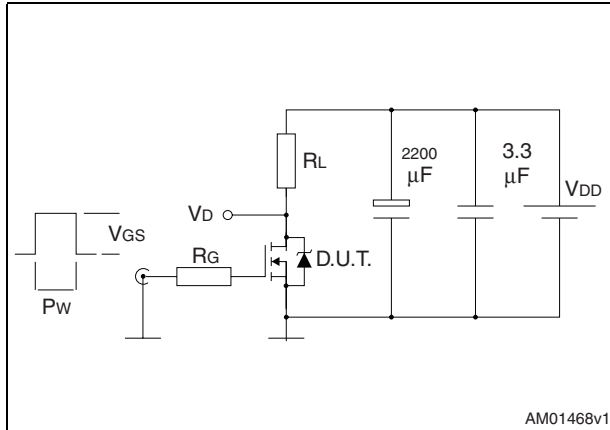


Figure 12. Source-drain diode forward characteristics

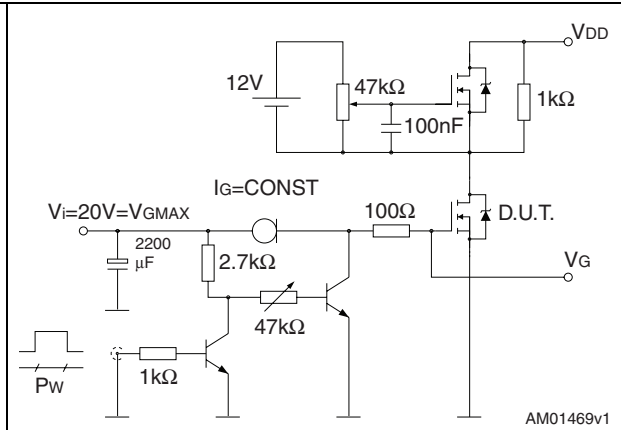


### 3 Test circuit

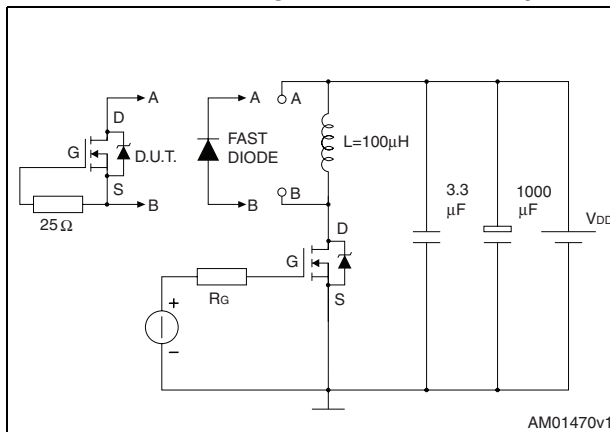
**Figure 13. Switching times test circuit for resistive load**



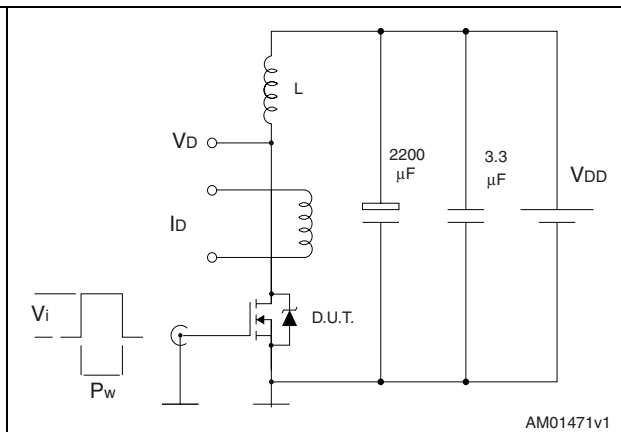
**Figure 14. Gate charge test circuit**



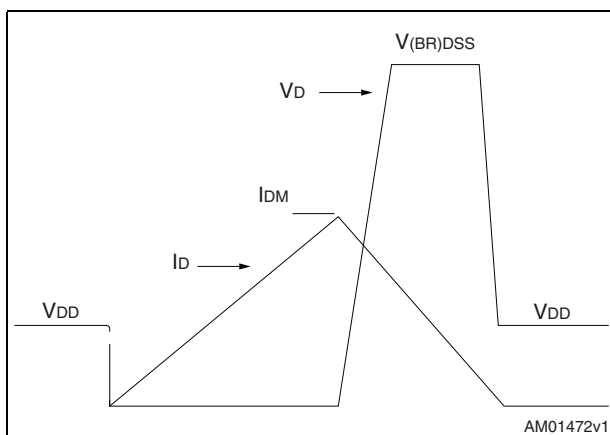
**Figure 15. Test circuit for inductive load switching and diode recovery times**



**Figure 16. Unclamped inductive load test circuit**



**Figure 17. Unclamped inductive waveform**



**Figure 18. Switching time waveform**

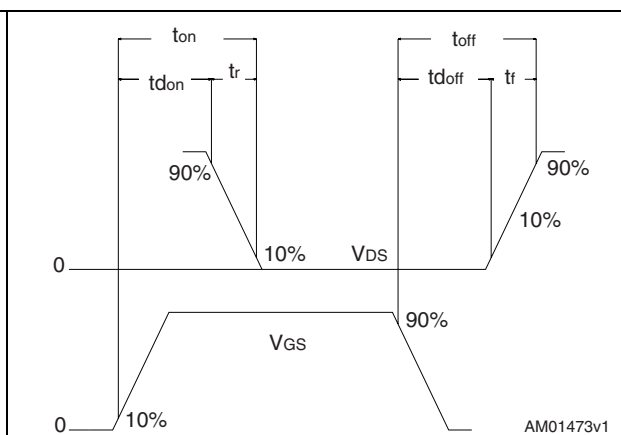
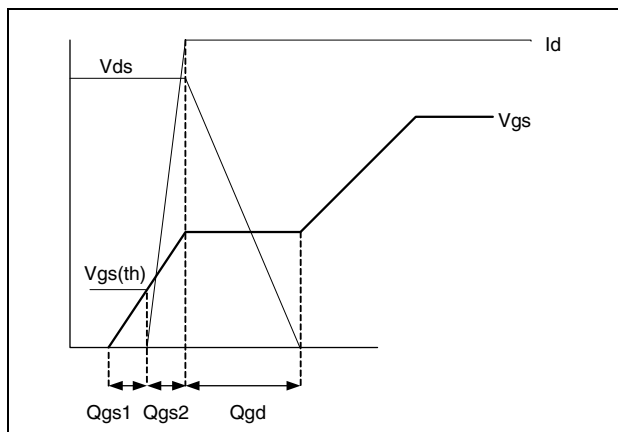




Figure 19. Gate charge waveform

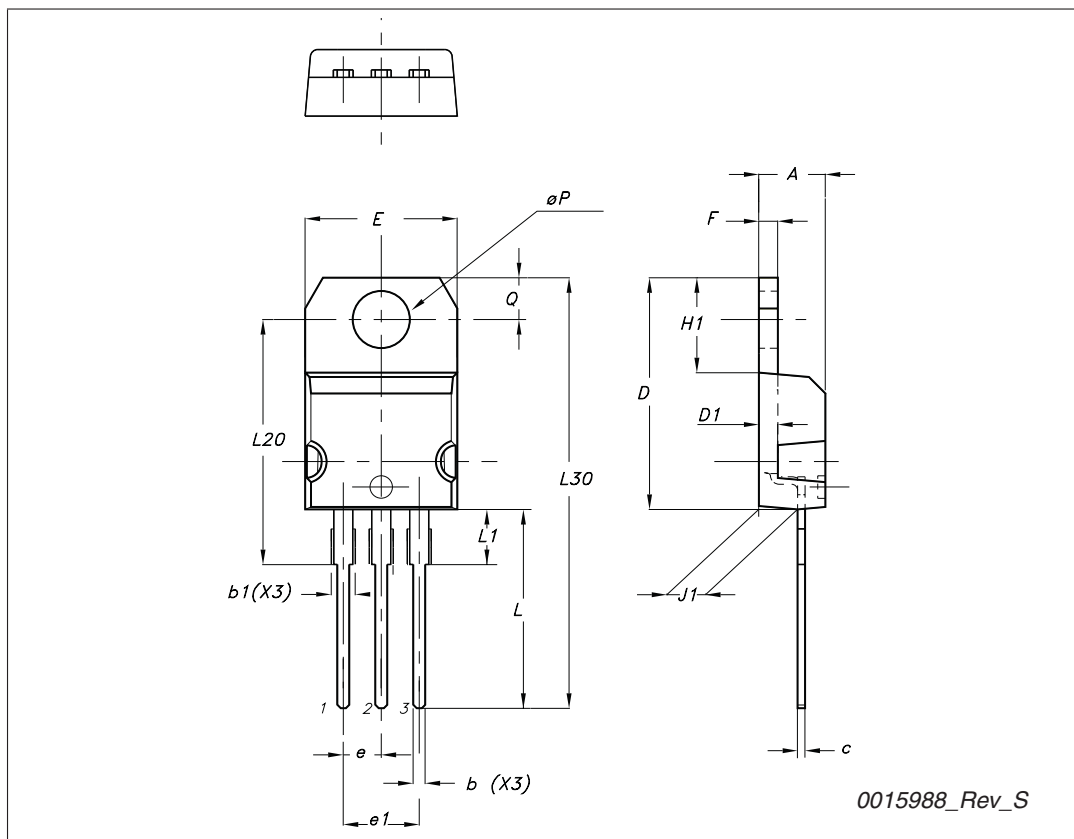


## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

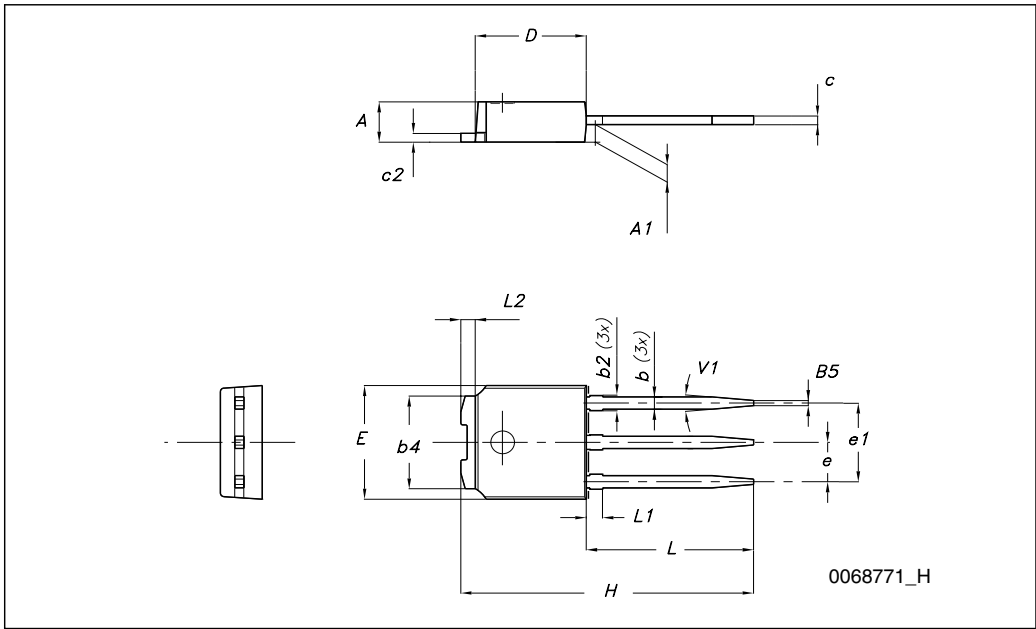
TO-220 type A mechanical data

Dim	mm		
	Min	Typ	Max
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
∅P	3.75		3.85
Q	2.65		2.95



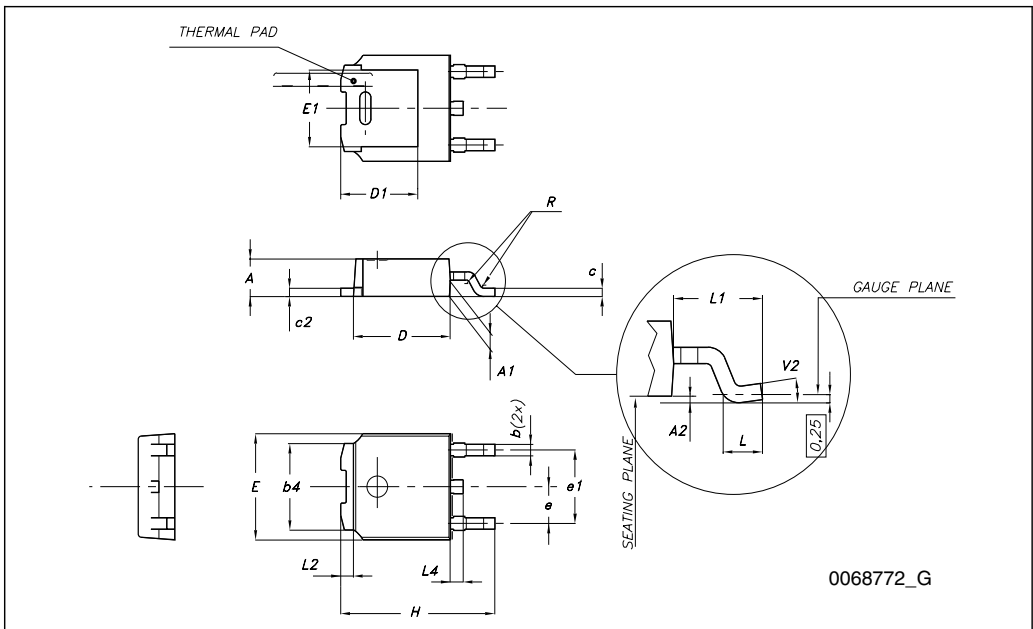
**TO-251 (IPAK) mechanical data**

DIM.	mm.		
	min.	typ	max.
A	2.20		2.40
A1	0.90		1.10
b	0.64		0.90
b2			0.95
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
E	6.40		6.60
e		2.28	
e1	4.40		4.60
H		16.10	
L	9.00		9.40
(L1)	0.80		1.20
L2		0.80	
V1		10°	



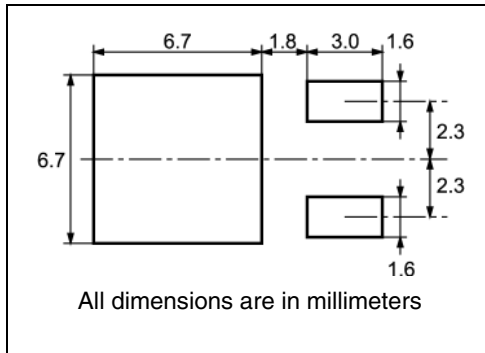
TO-252 (DPAK) mechanical data

DIM.	mm.		
	min.	typ	max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1		
L1		2.80	
L2		0.80	
L4	0.60		1
R		0.20	
V2	0°		8°



## 5 Packaging mechanical data

### DPAK FOOTPRINT



### TAPE AND REEL SHIPMENT

40 mm min. Access hole at slot location

Full radius

Tape slot in core for tape start 2.5mm min. width

G measured at hub

#### REEL MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	16.4	18.4	0.645	0.724
N	50		1.968	
T		22.4		0.881

BASE QTY	BULK QTY
2500	2500

#### TAPE MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	6.8	7	0.267	0.275
B0	10.4	10.6	0.409	0.417
B1		12.1		0.476
D	1.5	1.6	0.059	0.063
D1	1.5		0.059	
E	1.65	1.85	0.065	0.073
F	7.4	7.6	0.291	0.299
K0	2.55	2.75	0.100	0.108
P0	3.9	4.1	0.153	0.161
P1	7.9	8.1	0.311	0.319
P2	1.9	2.1	0.075	0.082
R	40		1.574	
W	15.7	16.3	0.618	0.641

10 pitches cumulative tolerance on tape +/- 0.2 mm

Center line of cavity

User Direction of Feed

FEED DIRECTION

Bending radius

R min.

For machine ref. only including draft and radii concentric around B0

## 6 Revision history

**Table 8. Document revision history**

Date	Revision	Changes
19-Oct-2007	1	First release
20-Feb-2008	2	Minor text changes to improve readability
21-Jul-2008	3	<ul style="list-style-type: none"> <li>– Added new package, mechanical data: TO-220</li> <li>– <a href="#">Figure 2: Safe operating area</a> has been corrected</li> <li>– <a href="#">Figure 7: Static drain-source on resistance</a> updated</li> <li>– New value on <a href="#">Table 2: Absolute maximum ratings</a></li> </ul>
20-Aug-2008	4	Added max value on $V_{GS(th)}$ ( <a href="#">Table 4</a> )
25-Sep-2008	5	$V_{GS}$ values has been changed on <a href="#">Table 2</a> and <a href="#">Table 4</a>
22-Jan-2009	6	Corrected value on <a href="#">Table 3: Thermal resistance</a>
01-Jul-2010	7	$V_{DS}$ values has been changed on <a href="#">Table 4</a>

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